



Product Overview

NTMS4807N: Power MOSFET 30V 14.8A 6.1 mOhm Single N-Channel SO-8

For complete documentation, see the data sheet

Product Description

This is a 30 V N-Channel Power MOSFET.

Features

- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- This is a Pb-Free Device
- Low  $R_{DS(on)}$  to Minimize Conduction Losses

Applications

- Disk Drives
- DC-DC Converters
- Printers

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	$V_{GS}^{(th)}$ Max (V)	$V_{GS}^{(th)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	$Q_g$ Typ @ $V_{GS} = 4.5$ V (nC)	$Q_g$ Typ @ $V_{GS} = 10$ V (nC)	$Q_{gd}$ Typ @ $V_{GS} = 4.5$ V (nC)	$Q_{rr}$ Typ (nC)	$C_{iss}$ Typ (pF)	$C_{oss}$ Typ (pF)	$C_{rss}$ Typ (pF)	Package Type
NTMS4807NR2G	Pb-free Halide free	Active	N-Channel	Single	30	20	3	14.8	2.5		7.5	6.1	24	46	10.4	23	2900	562	307	SOIC-8

For more information please contact your local sales support at [www.onsemi.com](http://www.onsemi.com)

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